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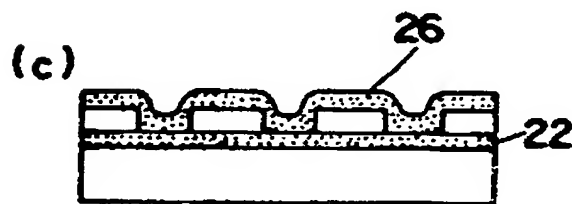
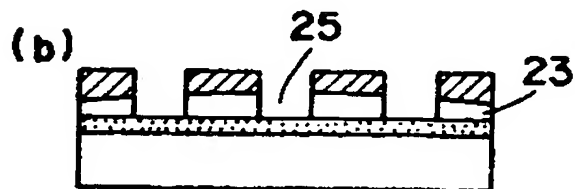
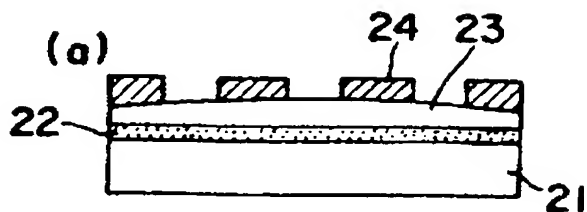
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APPLICANT : OKI ELECTRIC IND CO LTD;

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TITLE : MANUFACTURE OF
SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To enable to securely prevent the damage of a metallic wiring layer containing aluminum as the main constituent even without troublesome back surface treatment by etching an insulation film by means of the solution wherein HF, NH_4F and glacial acetic acid are mixed in a specific volume ratio.

CONSTITUTION: An intermediate insulation film 23 is formed over the entire surface of a substrate 21 including the upper part of the Al wiring layer 22. In case of boring contact holes in said film 23, first a photoresist pattern 24 is formed on said film 23, the film 23 is etched with said pattern as a mask. Here, the solution wherein HF, NH_4F and glacial acetic acid are mixed in the volume ratio of 1:9:1~3 is used for the etching. Thereby, the contact holes 25 are bored in said film 23. Thereafter, the photoresist pattern 24 is removed, and then the second Al wiring layer 26 is formed. This second Al wiring layer 26 is connected to the first one 22 through the contact windows 25.

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